



DMP4011SPSQ

40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	Ι _{D MAX} T _C = +25°C
-40V	10mΩ @ V _{GS} = -10V	-76A
	$14m\Omega @ V_{GS} = -4.5V$	-58A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

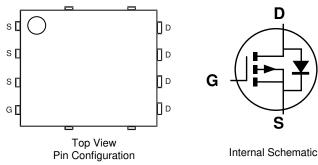
- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test In Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP4011SPSQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Top View

Part Number	Case	Packaging
DMP4011SPSQ -13	PowerDI5060-8	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Pin1

Marking Information



Bottom View

DII = Manufacturer's Marking P4011SP = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady	T _C = +25°C	- I _D	-76	А
Continuous Drain Current $V_{GS} = -10V$ (Note 7)	State	T _C = +70°C		-61	
Continuous Drain Current $V_{GS} = -10V$ (Note 6)	Steady State	T _A = +25°C	- I _D	-11.7	А
		$T_A = +70^{\circ}C$		-9.4	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-300	A		
Maximum Body Diode Continuous Current (Note 6)	Is	-8.9	A		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	-300	А		
Avalanche Current (Note 8) L = 1mH	I _{AS}	-22	A		
Avalanche Energy (Note 8) L = 1mH			E _{AS}	250	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	96.4	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	1.3	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

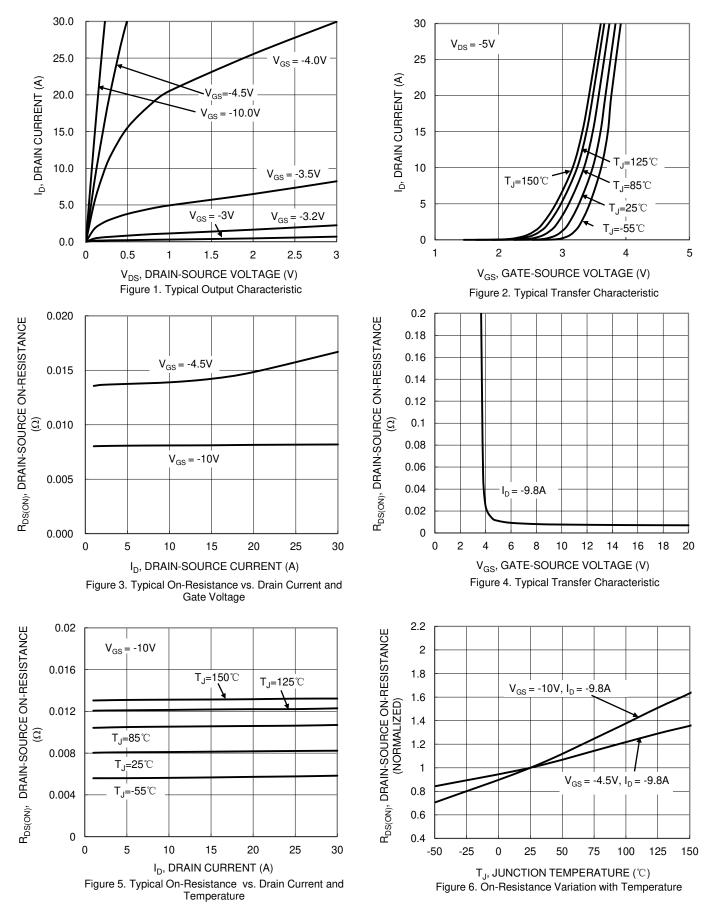
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-1.9	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		_	6	10	mΩ	V _{GS} = -10V, I _D = -9.8A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	10	14	11122	V _{GS} = -4.5V, I _D = -9.8A	
Diode Forward Voltage	V _{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)						-	
Input Capacitance	Ciss	_	2747			$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	508	_	pF		
Reverse Transfer Capacitance	Crss	_	222	_			
Gate Resistance	Rg	_	21.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qq		25				
Total Gate Charge (V _{GS} = -10V)	Qg	_	52	_	nC	$V_{DS} = -20V, I_D = -9.8A$	
Gate-Source Charge	Q _{gs}		8.5		no		
Gate-Drain Charge	Q _{gd}	_	11.8	_			
Turn-On Delay Time	t _{D(ON)}		6.6				
Turn-On Rise Time	t _R	_	6.5			$V_{GS} = -10V, V_{DD} = -20V$ $R_g = 6\Omega, I_D = -1A$	
Turn-Off Delay Time	t _{D(OFF)}	_	222		ns		
Turn-Off Fall Time	t _F	_	138			-	
Reverse Recovery Time	t _{RR}		25		ns	I _F = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q _{RR}	_	17	_	nC	I _F = -9.8A, di/dt = -100A/μs	

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}$ C. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to production testing.



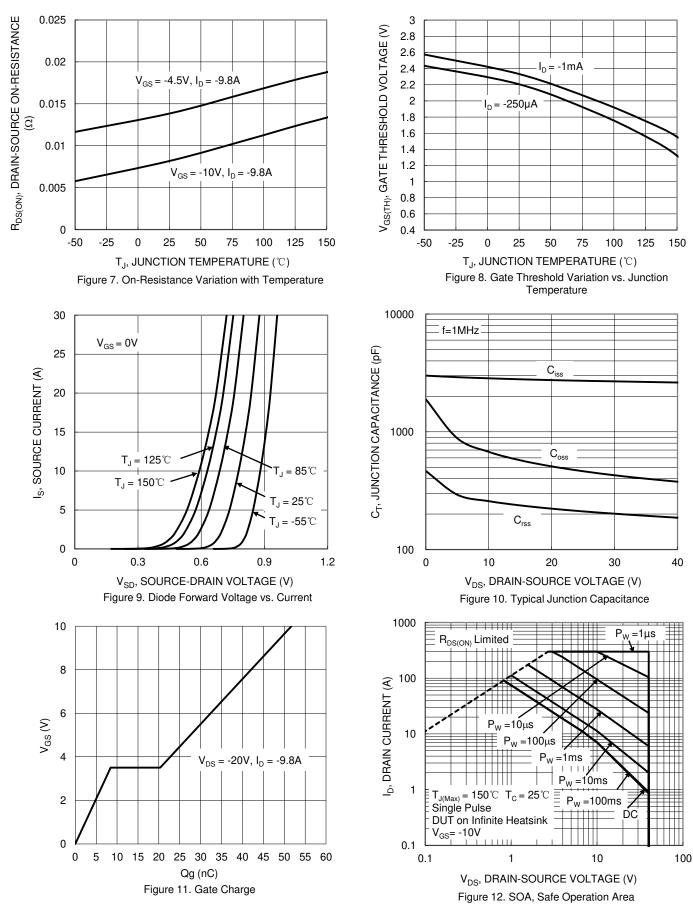
DMP4011SPSQ



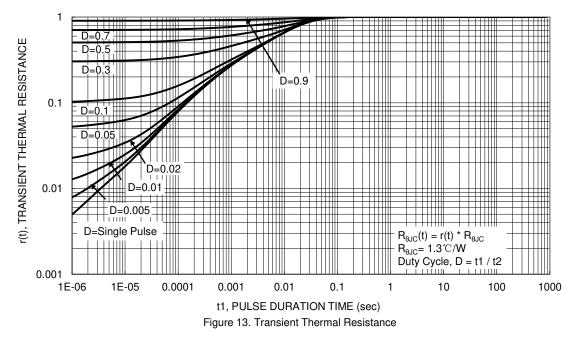
DMP4011SPSQ Document number: DS41321 Rev. 4 - 2



DMP4011SPSQ





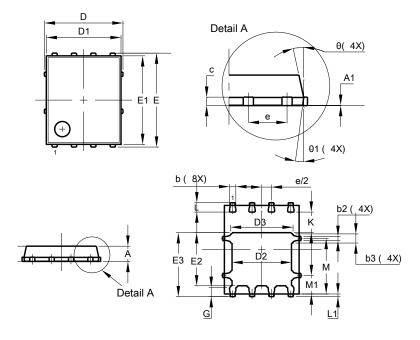




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

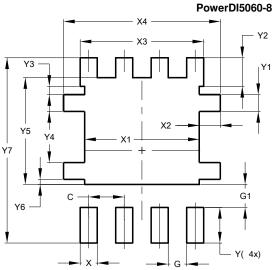
PowerDI5060-8



PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
e G		1.27 BSC			
	0.51	0.71	0.61		
К	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
Al	Dimens	ions in m	nm		

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
¥7	6.610			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com